

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	FDC5614P
▶ Overseas	Part Number	FDC5614P
▶ Equivalent	Part Number	FDC5614P

EV is the abbreviation of name EVVO

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

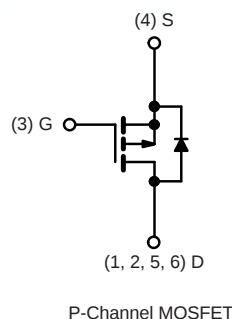
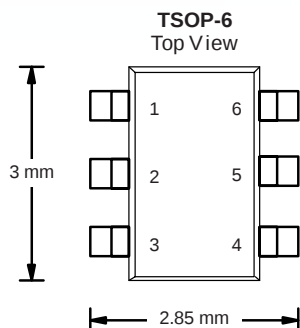
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 60	0.098 at $V_{GS} = - 10$ V	- 3.5	5.1 nC
	0.110 at $V_{GS} = - 4.5$ V	- 3.1	

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET

APPLICATIONS

- Load Switch



ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$)	I_D	- 3.5	A
		- 3.2	
		- 3.5 ^{b, c}	
		- 3.2 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 10	A
Continuous Source-Drain Diode Current	I_S	- 2.5	
		- 1.67 ^{b, c}	
Maximum Power Dissipation	P_D	3.0	W
		2.0	
		2.0 ^{b, c}	
		1.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	$t \leq 5$ s	R_{thJA}	55	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	41	

Notes:

a. Based on $T_C = 25\text{ }^\circ\text{C}$.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ s.

d. Maximum under Steady State conditions is 110 $^\circ\text{C/W}$.

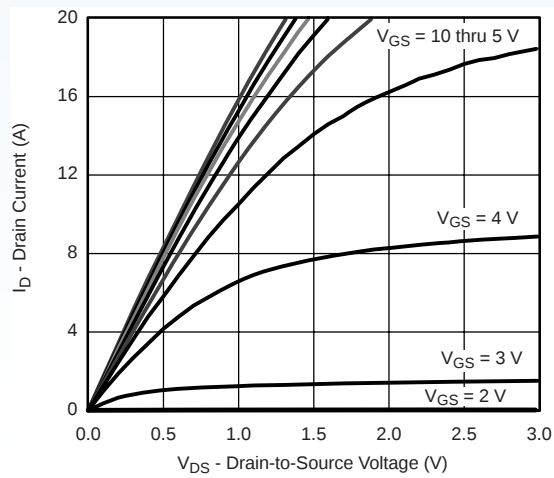
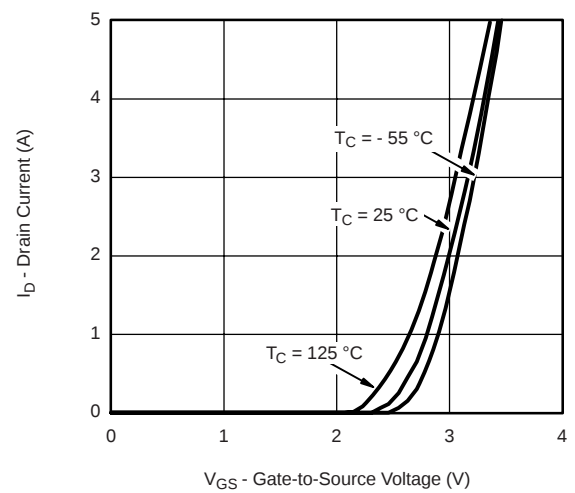
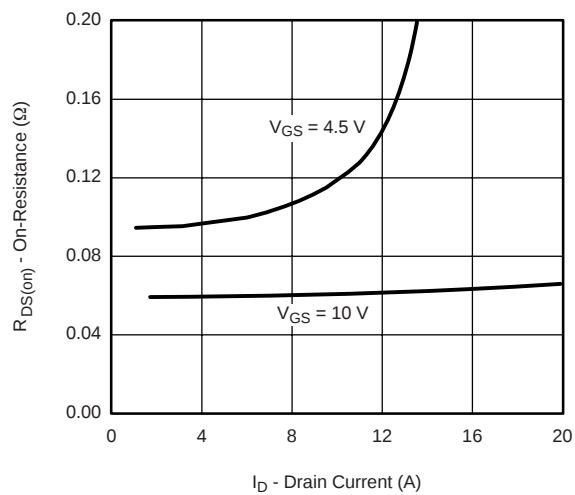
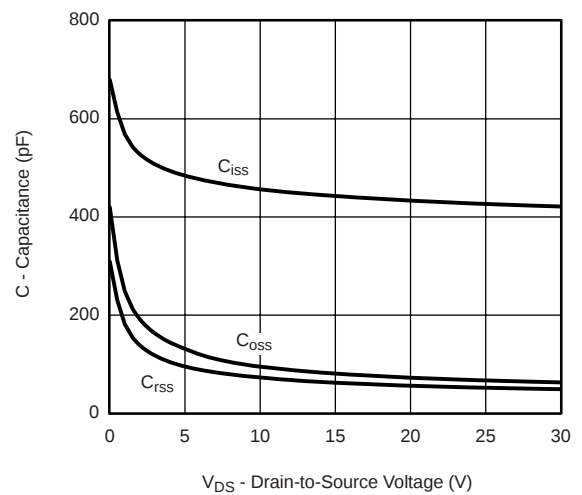
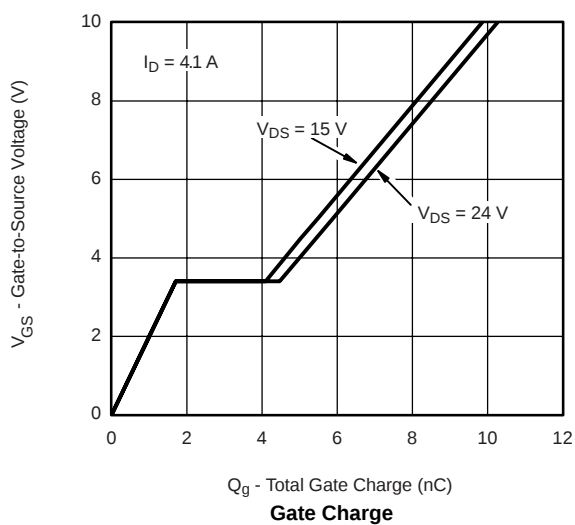
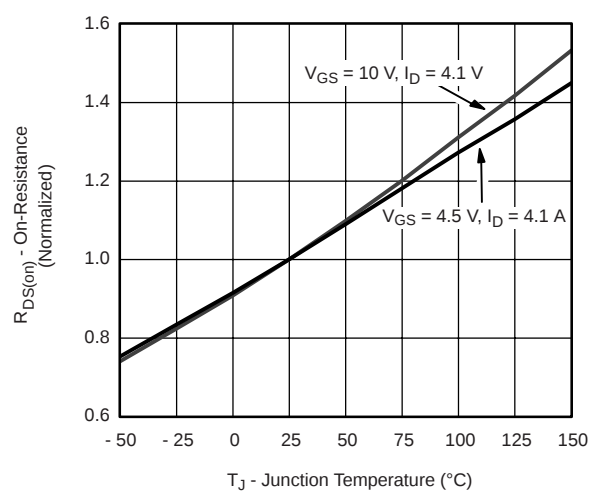
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	- 60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 31		mV/ $^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}$, $V_{GS} = -10\text{ V}$	- 10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -2.1\text{ A}$		0.075	0.098	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -2.1\text{ A}$		0.085	0.110	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -2.1\text{ A}$		8		S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		950		pF
Output Capacitance	C_{oss}			80		
Reverse Transfer Capacitance	C_{rss}			63		
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -2.1\text{ A}$		10	15	nC
Gate-Source Charge		$V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -2.1\text{ A}$		5.1	8	
Gate-Drain Charge	Q_{gd}			1.8		
Gate Resistance	R_g			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		7		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 4.6\text{ }\Omega$ $I_D \cong -2.3\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$		40	60	ns
Rise Time	t_r			80	120	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			12	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 4.6\text{ }\Omega$ $I_D \cong -2.3\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$		5	10	
Rise Time	t_r			13	20	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			- 2.5	A
Pulse Diode Forward Current ^a	I_{SM}				- 7	
Body Diode Voltage	V_{SD}	$I_S = -2.3\text{ A}$		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		20	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}			20	30	nC
Reverse Recovery Fall Time	t_a			14		ns
Reverse Recovery Rise Time	t_b			6		

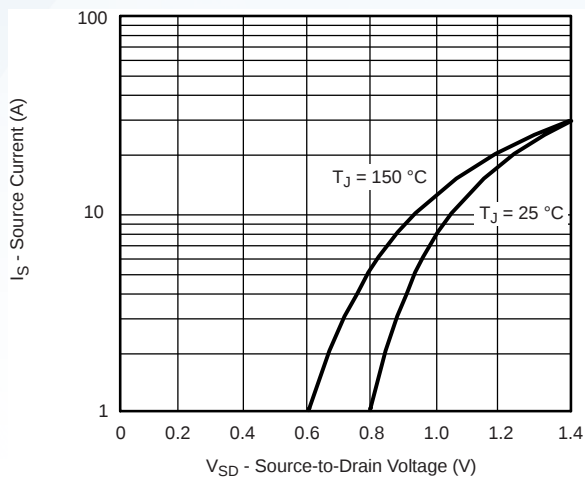
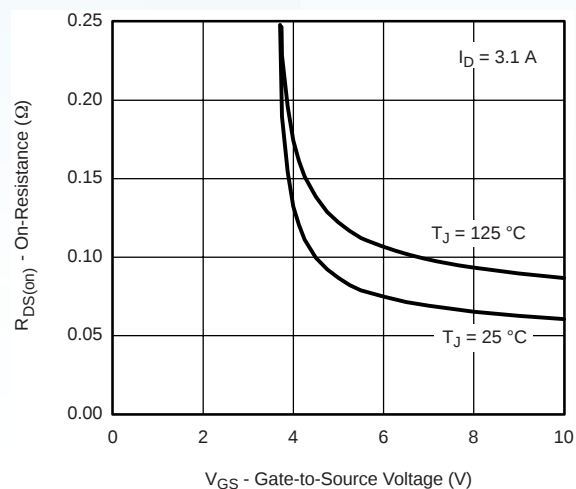
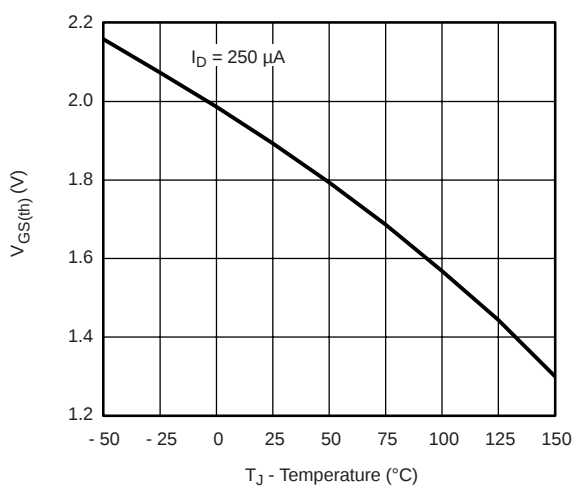
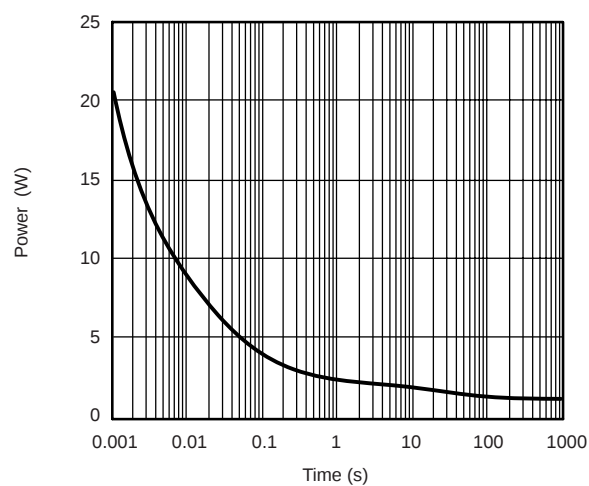
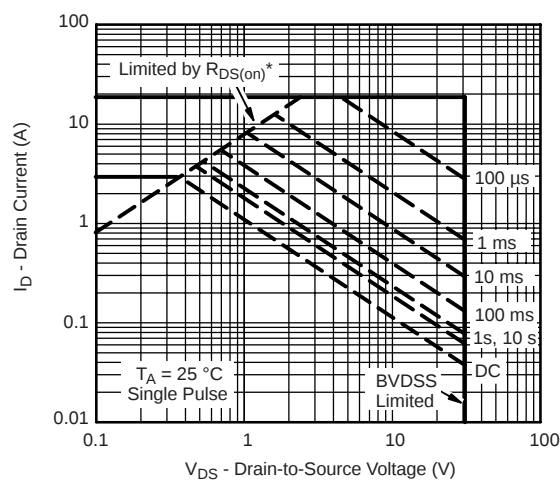
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

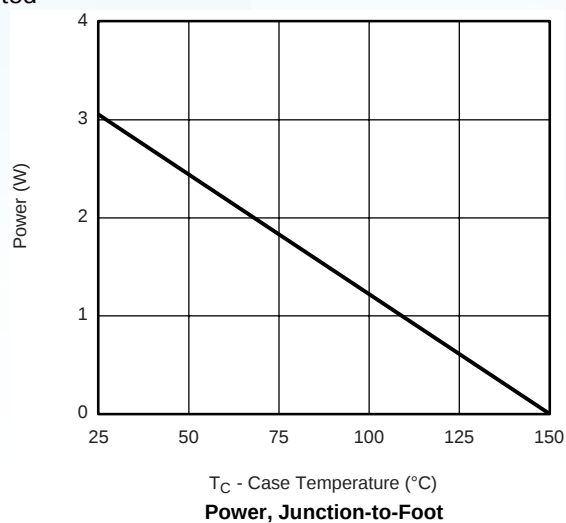
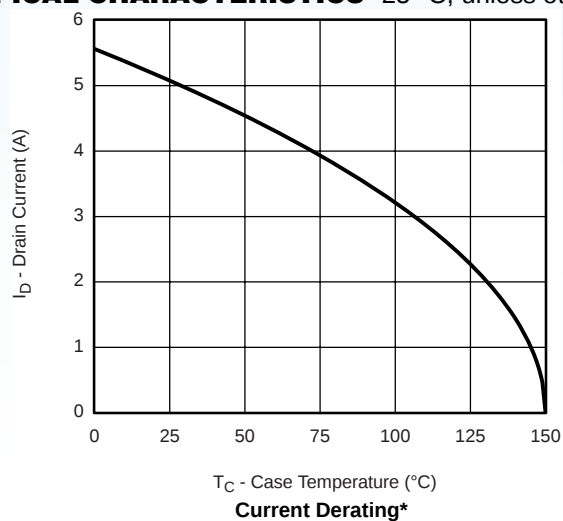
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

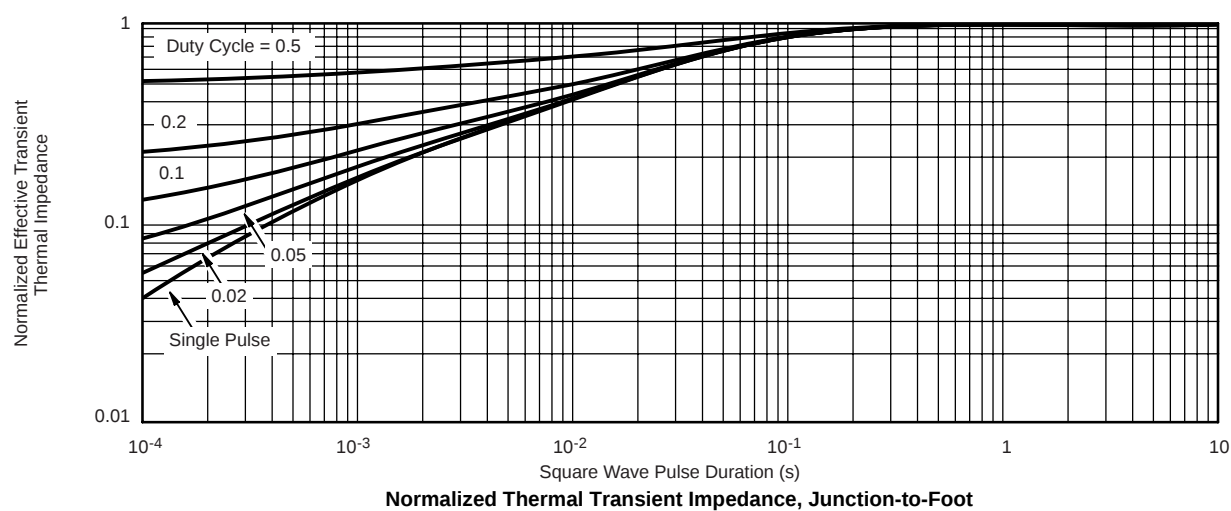
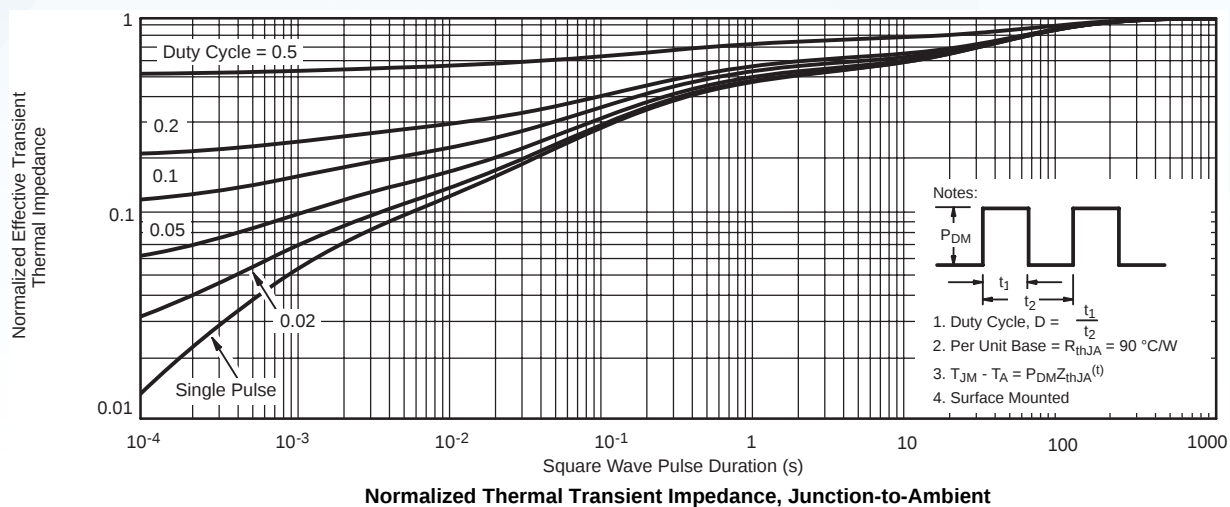
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

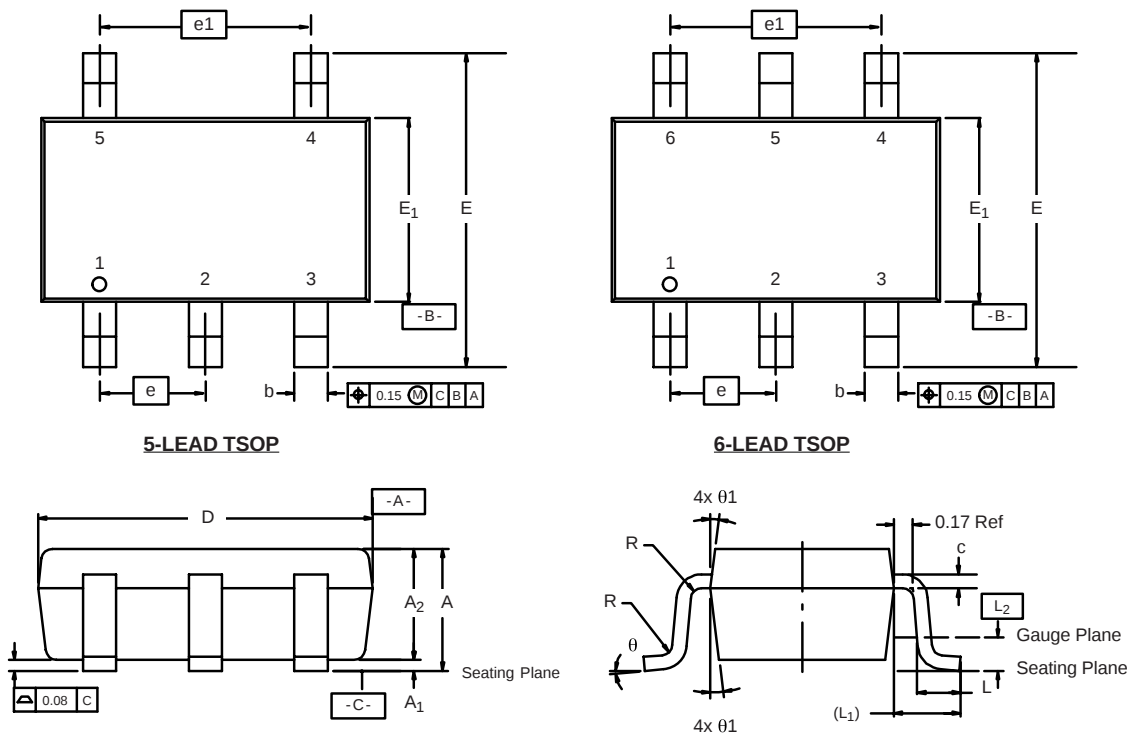
Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

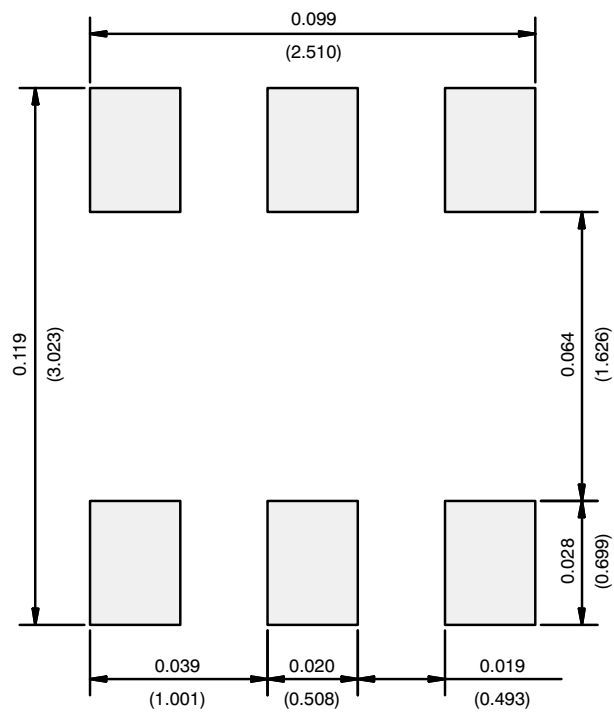
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TSOP: 5/6-LEAD
JEDEC Part Number: MO-193C



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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